

Product Summary

- Continuous Drain-Source Voltage: $V_{DS} = 60V$
- On-State Resistance: $500m\Omega$
- Max Nominal Load Current ($V_{IN} = 5V$): 1.1A
- Min Nominal Load Current ($V_{IN} = 5V$): 0.7A
- Clamping Energy: 550mJ

Description

The BSP75N-13/BSP75NTA is a self-protected, low-side IntelliFET® MOSFET. It features monolithic overtemperature, overcurrent, overvoltage (active clamp), and ESD protected logic-level functionality. It is intended as a general-purpose switch.

Applications

- Especially suited for loads with high inrush current, such as lamps and motors
- All types of resistive, inductive, and capacitive loads in switching applications
- μC compatible power switches for 12V and 24V DC applications
- Replaces electromechanical relays and discrete circuits
- Linear mode capabilities — current-limiting protection circuitry is designed to deactivate at low V_{DS} to not compromise the load current during normal operation. Maximum DC operating current is therefore determined by thermal capability of the package/board combination rather than by protection circuitry, which does not compromise the product's ability to self-protect at low V_{DS} .

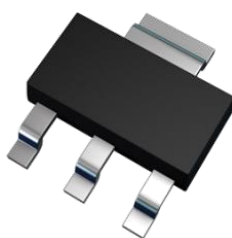
Features and Benefits

- Short-Circuit Protection with Auto Restart
- Overvoltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Overcurrent Protection
- Input Protection (ESD)
- Load-Dump Protection (Actively Protects Load)
- Logic-Level Input
- High Continuous Current Rating
- **Lead-Free Finish; RoHS Compliant (Note 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **An automotive-compliant part is available under a separate datasheet ([BSP75NQ-13/BSP75NQTA](#))**

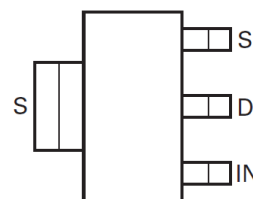
Mechanical Data

- Package: SOT223
- Package Material: Molded Plastic, "Green" Molding Compound
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish e3
- Weight: 0.112 grams (Approximate)

SOT223/SOT223 (Type DN)



Top View



Top View
Pin Out

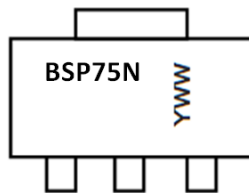
Ordering Information (Note 4)

Orderable Part Number	Package	Marking	Reel Size (inches)	Tape Width (mm)	Packing	
					Qty.	Carrier
BSP75N-13	SOT223	BSP75N	13	12	4,000	Reel
BSP75NTA	SOT223 (Type DN)	BSP75N	7	12	1,000	Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

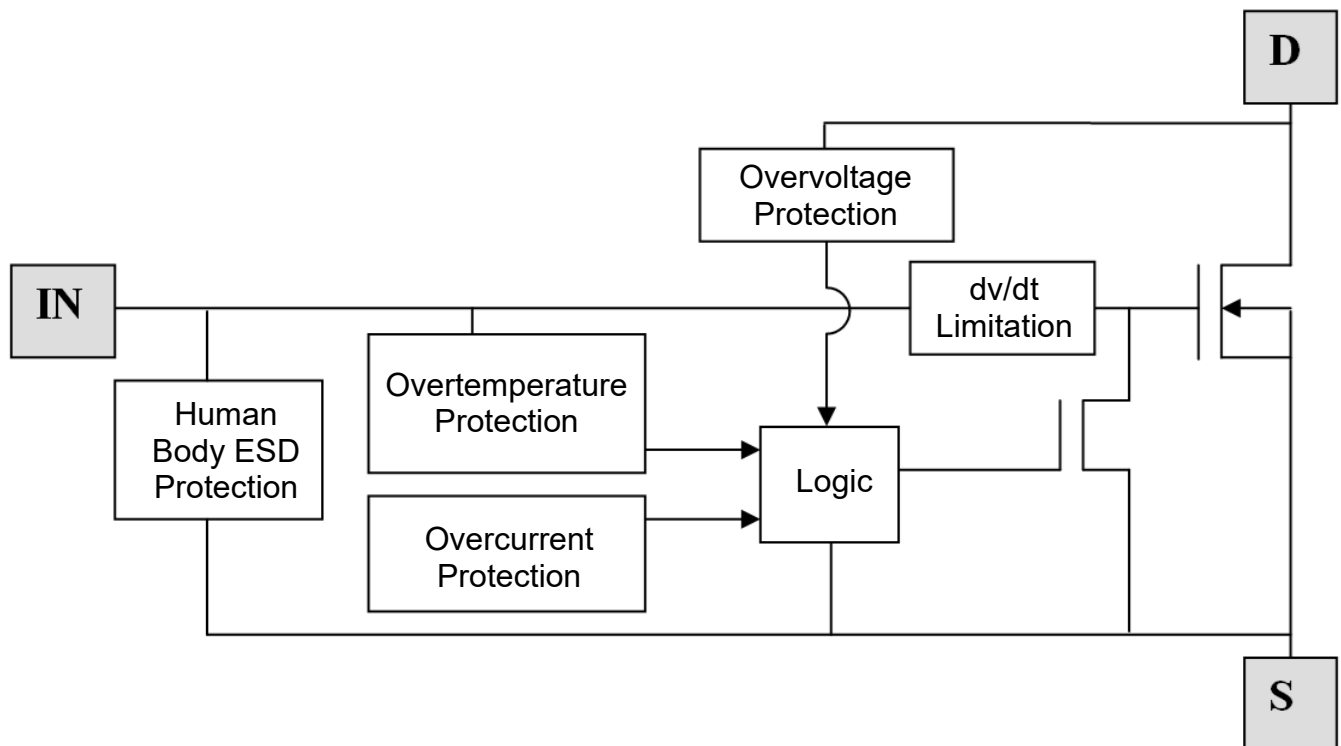
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Marking Information



BSP75N = Product Type Marking Code
 YWW = Date Code Marking
 Y or $\overline{Y}$ = Last Digit of Year (ex: 6 = 2026)
 WW or $\overline{WW}$ = Week Code (01 to 53)

Functional Block Diagram



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Parameter	Symbol	Value	Unit
Continuous Drain-Source Voltage	V _{DS}	60	V
Drain-Source Voltage for Short-Circuit Protection, V _{IN} = 5V	V _{DS(SC)}	36	V
Drain-Source Voltage for Short-Circuit Protection, V _{IN} = 10V	V _{DS(SC)}	20	V
Continuous Input Voltage	V _{IN}	-0.2 to 10	V
Peak Input Voltage	V _{IN}	-0.2 to 20	V
Operating Temperature Range	T _J	-40 to +150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C
Power Dissipation at T _A = +25°C (Note 5)	P _D	1.5	W
Power Dissipation at T _A = +25°C (Note 6)	P _D	0.6	W
Continuous Drain Current @ V _{IN} = 10V, T _A = +25°C (Note 5)	I _D	1.3	A
Continuous Drain Current @ V _{IN} = 5V, T _A = +25°C (Note 5)	I _D	1.1	A
Continuous Drain Current @ V _{IN} = 5V, T _A = +25°C (Note 6)	I _D	0.7	A
Continuous Source Current (Body Diode) (Note 5)	I _S	2.0	A
Pulsed Source Current (Body Diode) (Note 7)	I _S	3.3	A
Unclamped Single Pulse Inductive Energy	E _{AS}	550	mJ
Load Dump Protection	V _{LOAD_DUMP}	80	V
Electrostatic Discharge (Human Body Model)	V _{ESD}	4000	V
DIN Humidity Category, DIN 40 040	—	E	—
IEC Climatic Category, DIN IEC 68-1	—	40/150/56	—

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction to Ambient (Note 5)	R _{θJA}	83	°C/W
Junction to Ambient (Note 7)	R _{θJA}	45	°C/W
Junction to Ambient (Note 6)	R _{θJA}	208	°C/W

Notes:

5. For a device surface-mounted on 25mm x 25mm x 1.6mm FR-4 board with a high coverage of single-sided 2oz weight copper. Allocation of 6cm² copper 33% to source tab and 66% to drain pin with source tab and drain pin electrically isolated.
6. For a device surface-mounted on FR-4 board with the minimum copper required for electrical connections.
7. For a device surface-mounted on FR-4 board and measured at t ≤ 10s.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Conditions
Static Characteristics						
Drain-Source Clamp Voltage	V _{DS(AZ)}	60	70	75	V	I _D = 10mA
Off-State Drain Current	I _{DSS}	—	0.1	3	μA	V _{DS} = 12V, V _{IN} = 0
Off-State Drain Current	I _{DSS}	—	3	15	μA	V _{DS} = 32V, V _{IN} = 0
Input Threshold Voltage (Note 8)	V _{IN(TH)}	1	2.1	—	V	V _{DS} = V _{GS} , I _D = 1mA
Input Current	I _{IN}	—	0.7	1.2	mA	V _{IN} = 5V
Input Current	I _{IN}	—	1.5	2.7	mA	V _{IN} = 7V
Input Current	I _{IN}	—	4	7	mA	V _{IN} = 10V
Static Drain-Source On-State Resistance	R _{DS(ON)}	—	520	675	mΩ	V _{IN} = 5V, I _D = 0.7A
Static Drain-Source On-State Resistance	R _{DS(ON)}	—	385	550	mΩ	V _{IN} = 10V, I _D = 0.7A
Current Limit (Note 9)	I _{D(LIM)}	0.7	1.0	1.5	A	V _{IN} = 5V, V _{DS} > 5V
Current Limit (Note 9)	I _{D(LIM)}	1	1.8	2.3	A	V _{IN} = 10V, V _{DS} > 5V
Dynamic Characteristics						
Turn-On Time (V _{IN} to 90% I _D)	t _{ON}	—	3	—	μs	R _L = 22Ω, V _{IN} = 0 to 10V V _{DD} = 12V
Turn-Off Time (V _{IN} to 90% I _D)	t _{OFF}	—	13	—	μs	R _L = 22Ω, V _{IN} = 10V to 0 V _{DD} = 12V
Slew Rate On (70% to 50% V _{DD})	-dv _{DS} /dt _{ON}	—	8	—	V/μs	R _L = 22Ω, V _{IN} = 0 to 10V V _{DD} = 12V
Slew Rate Off (50% to 70% V _{DD})	dv _{DS} /dt _{ON}	—	3.2	—	V/μs	R _L = 22Ω, V _{IN} = 10V to 0 V _{DD} = 12V
Protection Functions (Note 10)						
Minimum Input Voltage for Overtemperature Protection	V _{PROT}	4.5	—	—	V	—
Thermal Overload Trip Temperature	T _{JT}	+150	+175	—	°C	—
Thermal Hysteresis	—	—	+1	—	°C	—
Unclamped Single Pulse Inductive Energy T _J = +25°C	E _{AS}	550	—	—	mJ	I _{D(ISO)} = 0.7A, V _{DD} = 32V
Unclamped Single Pulse Inductive Energy T _J = +150°C	E _{AS}	200	—	—	mJ	I _{D(ISO)} = 0.7A, V _{DD} = 32V
Inverse Diode						
Source-Drain Voltage	V _{SD}	—	—	1	V	V _{IN} = 0, -I _D = 1.4A

- Notes:
- Protection features may operate outside spec for V_{IN} < 4.5V.
 - The drain current is limited to a reduced value when V_{DS} exceeds a safe level.
 - Integrated protection functions are designed to prevent IC destruction under fault conditions described in the datasheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous, repetitive operation.

Application Information

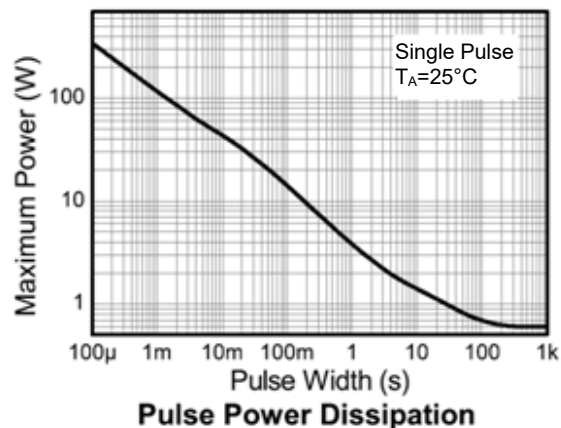
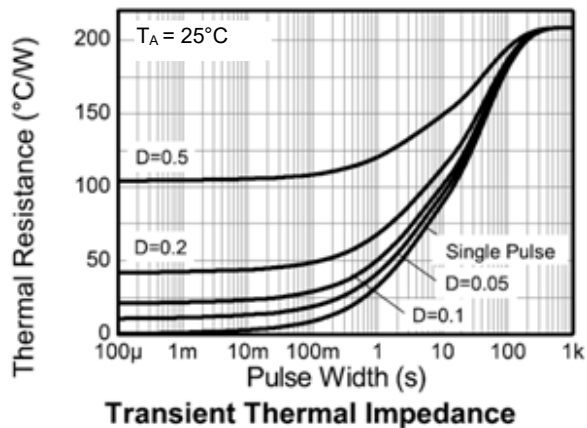
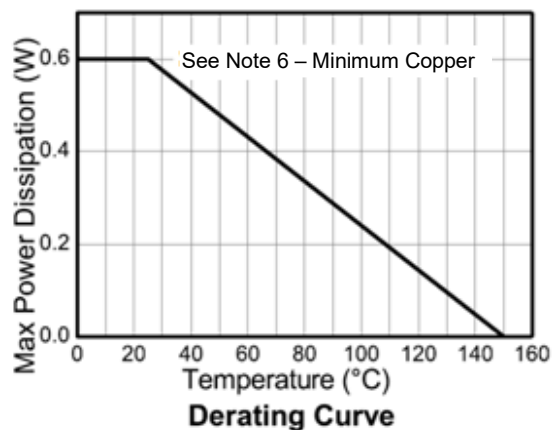
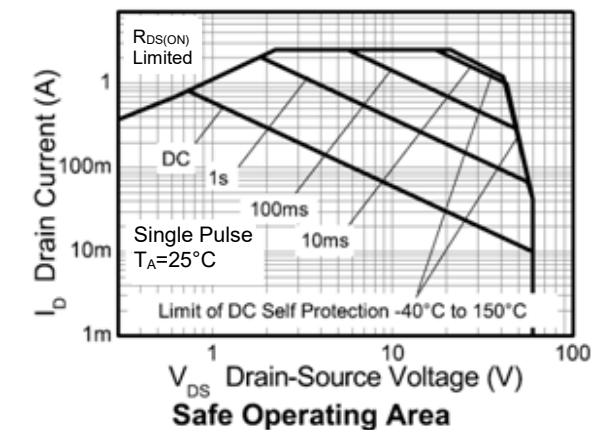
The current-limit protection circuitry is designed to deactivate at low V_{DS} to prevent the load current from being unnecessarily restricted during normal operation. The design max DC operating current is therefore determined by the thermal capability of the package/board combination rather than by the protection circuitry (see *Typical Characteristics* graphs). This does not compromise the product's ability to self-protect at low V_{DS} .

The overtemperature protection circuit trips at a minimum of $+150^{\circ}\text{C}$, so the available package dissipation reduces as the maximum required ambient temperature increases. This leads to the following maximum recommended continuous operating currents.

Minimum Copper Area Characteristics

For minimum copper condition as described in Note 6.

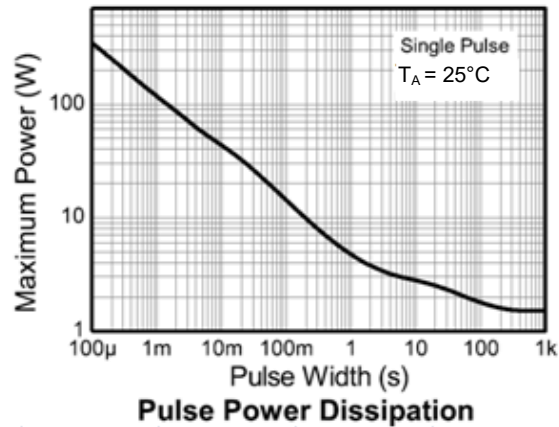
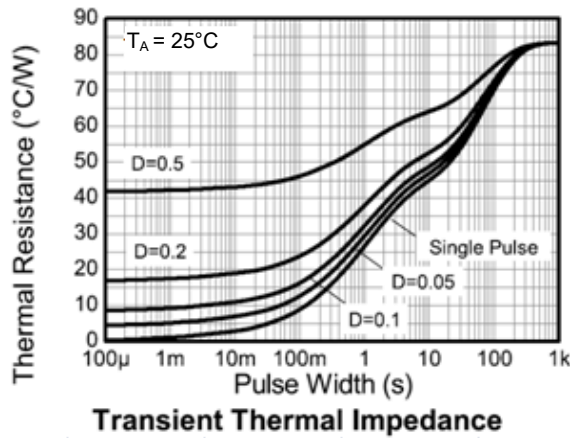
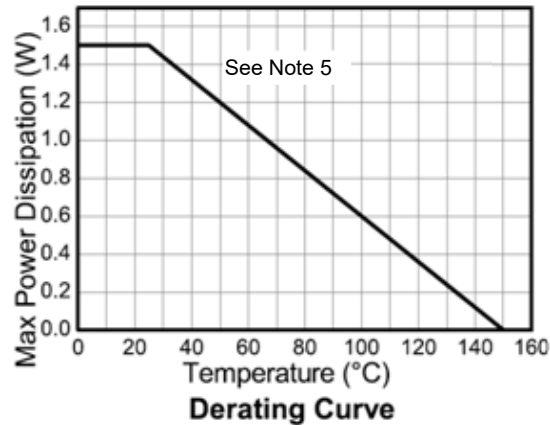
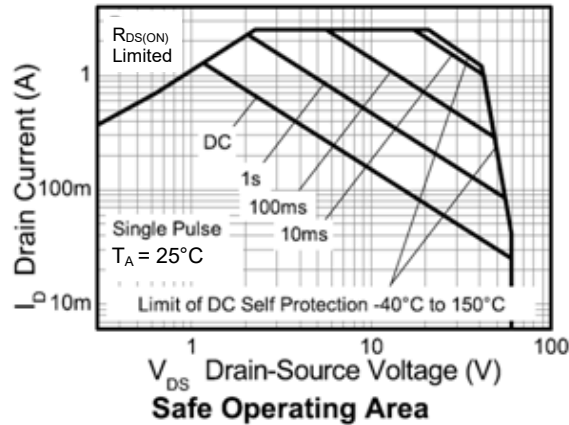
Max Ambient Temperature T_A	Maximum Continuous Current	
	$V_{IN} = 5\text{V}$	$V_{IN} = 10\text{V}$
$+25^{\circ}\text{C}$	720mA	840mA
$+70^{\circ}\text{C}$	575mA	670mA
$+85^{\circ}\text{C}$	520mA	605mA
$+125^{\circ}\text{C}$	320mA	375mA



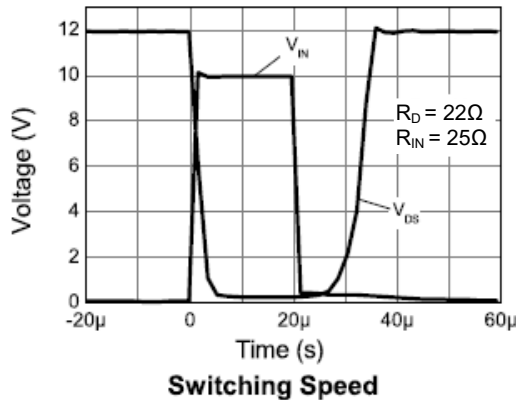
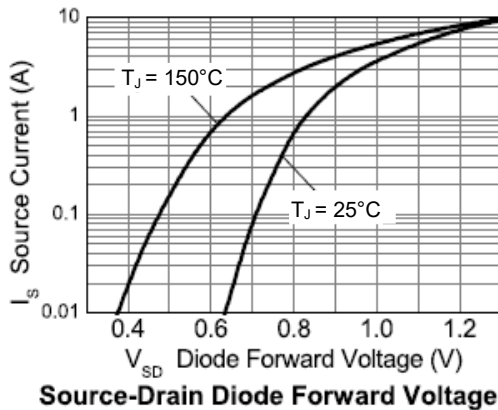
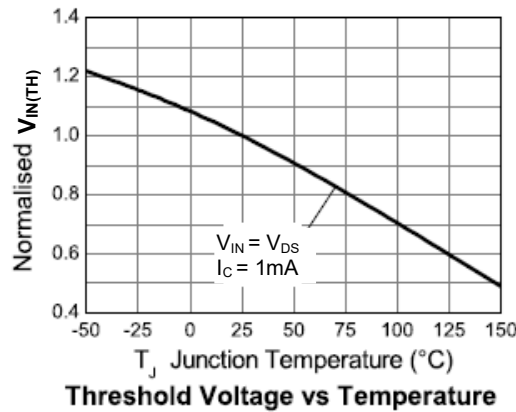
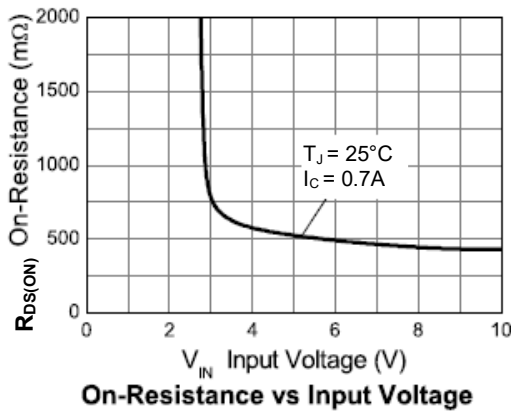
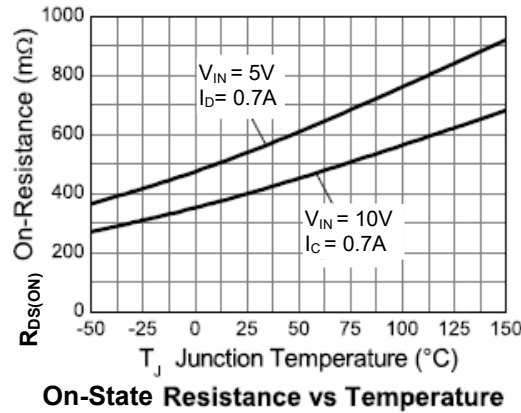
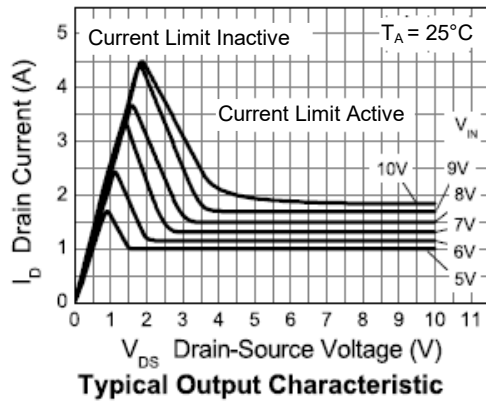
Large Copper Area Characteristics

For large copper area as described in Note 5.

Max Ambient Temperature T_A	Maximum Continuous Current	
	$V_{IN} = 5V$	$V_{IN} = 10V$
+25°C	1140mA	1325mA
+70°C	915mA	1060mA
+85°C	825mA	955mA
+125°C	510mA	590mA



Typical Characteristics

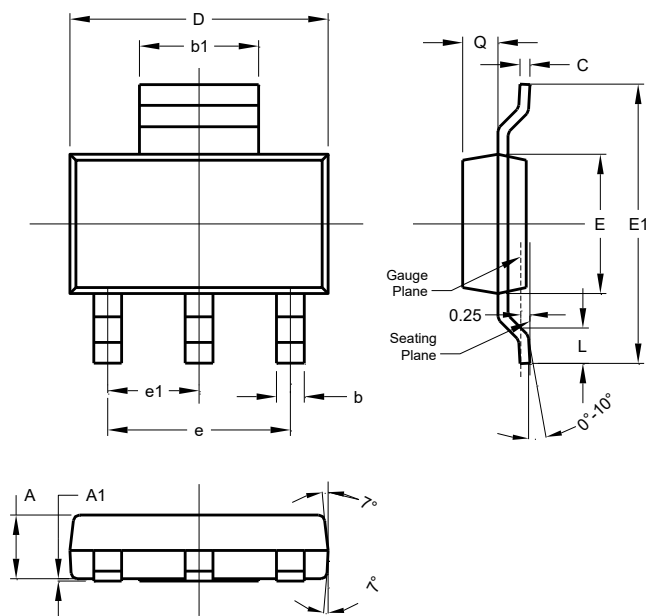


Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Package Type 1:

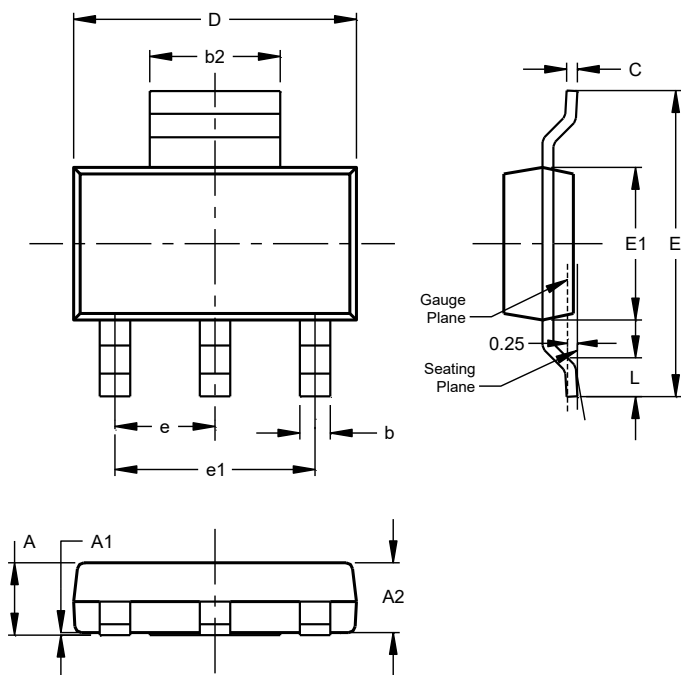
SOT223



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Package Type 2:

SOT223 (Type DN)



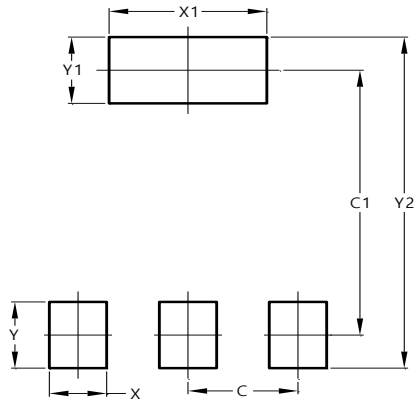
SOT223 (Type DN)			
Dim	Min	Max	Typ
A	--	1.70	--
A1	0.01	0.15	--
A2	1.50	1.68	1.60
b	0.60	0.80	0.70
b2	2.90	3.10	--
c	0.20	0.32	--
D	6.30	6.70	--
E	6.70	7.30	--
E1	3.30	3.70	--
e	--	--	2.30
e1	--	--	4.60
L	0.85	--	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Package Type 1:

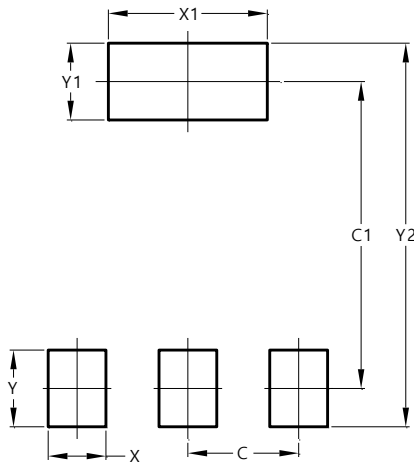
SOT223



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Package Type 2:

SOT223 (Type DN)



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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